

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-31 (Cancelled).

Claim 32 (Previously Presented): A ceramic substrate having a conductor formed inside thereof for a semiconductor producing/examining device,

wherein:

a ceramic layer including said conductor and the vicinity thereof and a ceramic layer located lower than said conductor exhibit a state of intergranular fracture at the time of fracture; and

a ceramic layer other than said ceramic layers exhibits a state of intragranular fracture at the time of fracture.

Claim 33 (Previously Presented): The ceramic substrate for a semiconductor producing/examining device according to Claim 32,

wherein said ceramic substrate comprises nitride ceramic or carbide ceramic.

Claim 34 (Previously Presented): The ceramic substrate for a semiconductor producing/examining device according to Claim 32,

wherein said ceramic substrate has a thickness of 20 mm or less.

Claim 35 (Previously Presented): The ceramic substrate for a semiconductor producing/examining device according to Claim 32,

wherein said ceramic substrate has a disc-like shape and a diameter of 200 mm or more.

Claim 36 (Previously Presented): The ceramic substrate for a semiconductor producing/examining device according to Claim 32,
wherein said ceramic substrate is used at a temperature of 150°C or higher.

Claim 37 (Previously Presented): The ceramic substrate for a semiconductor producing/examining device according to Claim 32,
wherein said ceramic substrate has an electrostatic electrode or an RF electrode.

Claim 38 (Previously Presented): The ceramic substrate for a semiconductor producing/examining device according to Claim 32,
wherein said conductor is a metal foil, a metal wire, or a sintered body of metal particles.

Claim 39 (Previously Presented): The ceramic substrate for a semiconductor producing/examining device according to Claim 32,
wherein the average grain diameter of a ceramic grain of said ceramic substrate is 3 μm or less.

Claim 40 (Previously Presented): The ceramic substrate for a semiconductor producing/examining device according to Claim 32,
wherein the average grain diameter of a ceramic grain of said ceramic substrate is 2 μm or less.

Claim 41 (Previously Presented): The ceramic substrate for a semiconductor producing/examining device according to Claim 32,
wherein said ceramic substrate contains oxygen.

Claim 42 (Previously Presented): The ceramic substrate for a semiconductor producing/examining device according to Claim 32,
wherein said ceramic substrate contains 0.05 to 10 weight % of oxygen.

Claim 43 (Previously Presented): The ceramic substrate for a semiconductor producing/examining device according to Claim 32,
wherein said ceramic substrate contains sulfur.

Claim 44 (Previously Presented): The ceramic substrate for a semiconductor producing/examining device according to Claim 32,
wherein said ceramic substrate contains 0.05 to 200 ppm of sulfur.

Claim 45 (Previously Presented): The ceramic substrate for a semiconductor producing/examining device according to Claim 32,
wherein said ceramic substrate contains an oxide.

Claim 46 (Previously Presented): The ceramic substrate for a semiconductor producing/examining device according to Claim 32,
wherein said ceramic substrate contains an oxide of a rare earth element.

Claim 47 (Previously Presented): The ceramic substrate for a semiconductor producing/examining device according to Claim 32,
which is used as a ceramic heater.

Claim 48 (Previously Presented): An electrostatic chuck having an electrostatic electrode and a resistance heating element formed inside a ceramic substrate thereof,
wherein:

a ceramic layer including said electrostatic electrode and the vicinity thereof and a ceramic layer located lower than said electrostatic electrode exhibit a state of intergranular fracture at the time of fracture; and

a ceramic layer other than said ceramic layers exhibits a state of intragranular fracture at the time of fracture.

Claim 49 (Previously Presented): The electrostatic chuck according to Claim 48,
wherein said ceramic substrate comprises nitride ceramic or carbide ceramic.

Claim 50 (Previously Presented): The electrostatic chuck according to Claim 48,
wherein said ceramic substrate has a thickness of 20 mm or less.

Claim 51 (Previously Presented): The electrostatic chuck according to Claim 48,
wherein said ceramic substrate has a disc-like shape and a diameter of 200 mm or more.

Claim 52 (Previously Presented): The electrostatic chuck according to Claim 48,
wherein said ceramic substrate is used at a temperature of 150°C or higher.

Claim 53 (Previously Presented): The electrostatic chuck according to Claim 48, wherein said ceramic substrate has an RF electrode.

Claim 54 (Previously Presented): The electrostatic chuck according to Claim 48, wherein said heating element is a metal foil, a metal wire, or a sintered body of metal particles.

Claim 55 (Previously Presented): The electrostatic chuck according to Claim 48, wherein the average grain diameter of a ceramic grain of said ceramic substrate is 3 μm or less.

Claim 56 (Previously Presented): The electrostatic chuck according to Claim 48, wherein the average grain diameter of a ceramic grain of said ceramic substrate is 2 μm or less.

Claim 57 (Previously Presented): The electrostatic chuck according to Claim 48, wherein said ceramic substrate contains oxygen.

Claim 58 (Previously Presented): The electrostatic chuck according to Claim 48, wherein said ceramic substrate contains 0.05 to 10 weight % of oxygen.

Claim 59 (Previously Presented): The electrostatic chuck according to Claim 48, wherein said ceramic substrate contains sulfur.

Claim 60 (Previously Presented): The electrostatic chuck according to Claim 48, wherein said ceramic substrate contains 0.05 to 200 ppm of sulfur.

Claim 61 (Previously Presented): The electrostatic chuck according to Claim 48, wherein said ceramic substrate contains an oxide.

Claim 62 (Previously Presented): The electrostatic chuck according to Claim 48, wherein said ceramic substrate contains an oxide of a rare earth element.

Claim 63 (Previously Presented): The electrostatic chuck according to Claim 48, which is used as a ceramic heater.

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DISCUSSION OF THE AMENDMENT

Claims 17-31 have been cancelled.

No new matter has been added by the above amendment. Claims 32-63 are now pending in the application.